

The diagram illustrates a cross-section of a SiGe heterostructure with a nitride spacer. The structure is built on a substrate of **N doped Si**. The layers, from bottom to top, are:

- N doped Si**: The substrate layer.
- epi recessed E&SD**: A layer of **N doped Si** that is recessed in the center.
- thin Si**: A thin layer of **N doped Si** that covers the recessed area.
- SiGe**: A layer of **N doped SiGe** that is grown on top of the thin Si layer.
- nitride**: A layer of **Nitride** that is grown on top of the SiGe layer.

Labels and arrows indicate the following components:

- As implant**: Points to the **N doped Si** layer.
- epi recessed E&SD**: Points to the recessed **N doped Si** layer.
- thin Si**: Points to the thin **N doped Si** layer.
- SiGe**: Points to the **N doped SiGe** layer.
- nitride**: Points to the **Nitride** layer.
- N doped**: Points to the **N doped Si** layer.
- epi Si spacers**: Points to the **N doped Si** layer.

Figure 7

8/27
FIS920030371US1

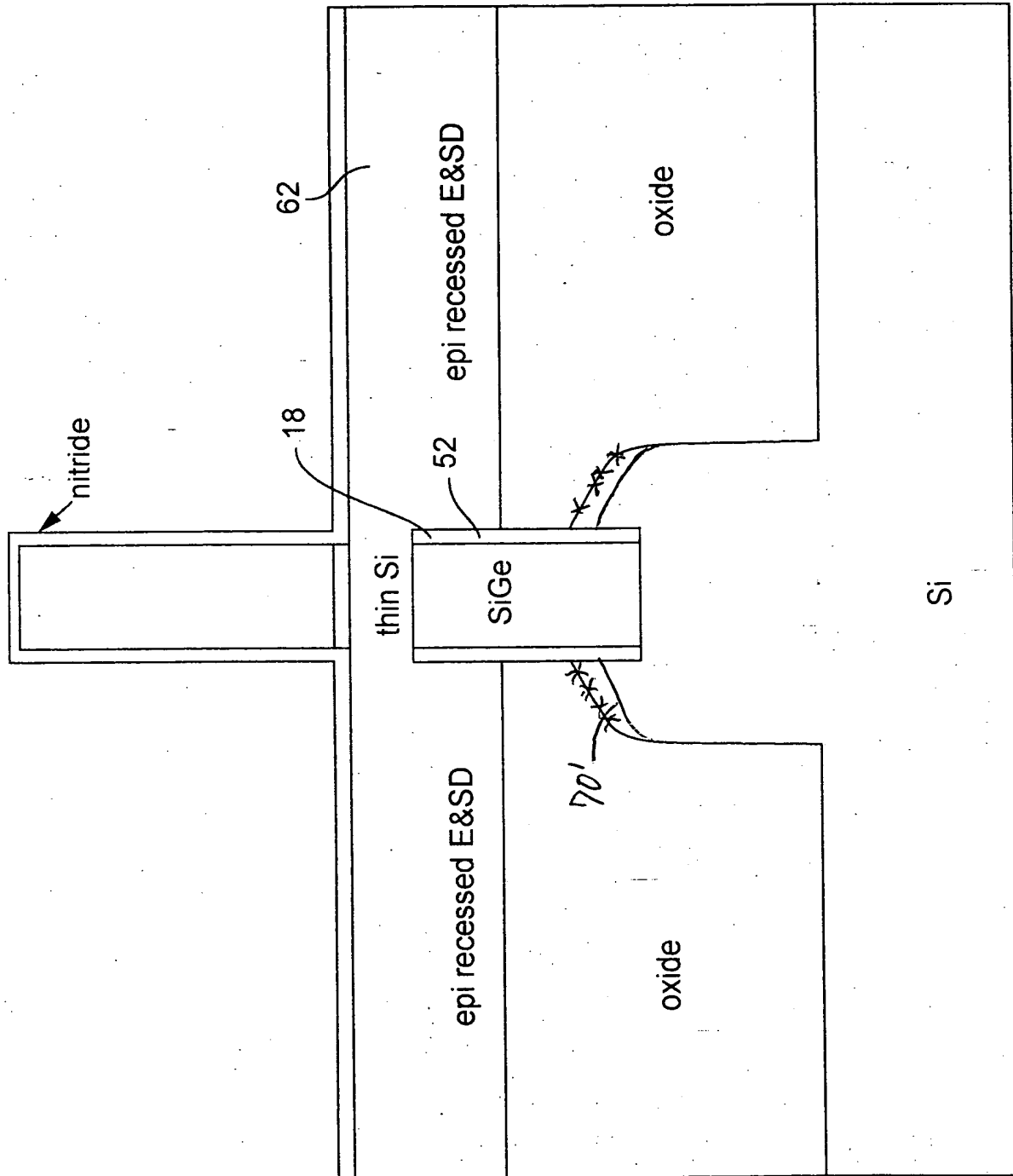


Figure 8